SLLS151C - DECEMBER 1988 - REVISED MARCH 1997

- Meets or Exceeds the Requirements of ANSI EIA/TIA-232-E and ITU Recommendation V.28
- Very Low Power Consumption 5 mW Typ
- Wide Driver Supply Voltage . . . ±4.5 V to ±15 V
- Driver Output Slew Rate Limited to 30 V/us Max
- Receiver Input Hysteresis . . . 1000 mV Typ
- Push-Pull Receiver Outputs
- On-Chip Receiver 1-μs Noise Filter
- Functionally interchangeable With Motorola MC145404

#### (TOP VIEW) D<sub>VCC</sub> $V_{\text{DD}}$ 1RA 🛚 2 19 1 1RY 1DY 🛮 18 🛮 1DA 3 2RA 4 17 ∐2RY 2DY [ 5 16 N2DA 15 3RY 3RA 🛛 6 3DY **∏** 7 14 **∏** 3DA 4RA Π 13 **∏** 4RY 8 4DY $\Pi$ 9 12 **∏** 4DA 11 GND ۷<sub>SS</sub> 🛚 10

DW OR N PACKAGE

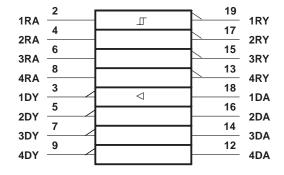
### description

The SN75C1154 is a low-power BiMOS device containing four independent drivers and receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). This device has been designed to conform to ANSI EIA/TIA-232-E. The drivers and receivers of the SN75C1154 are similar to those of the SN75C188 quadruple driver and SN75C189A quadruple receiver, respectively. The drivers have a controlled output slew rate that is limited to a maximum of  $30 \text{ V/}\mu\text{s}$  and the receivers have filters that reject input noise pulses of shorter than 1  $\mu\text{s}$ . Both these features eliminate the need for external components.

The SN75C1154 is designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in these devices interface to single inputs of peripheral devices such as ACEs, UARTs, or microprocessors. By using sampling, such peripheral devices are usually insensitive to the transition times of the input signals. If this is not the case or for other uses, it is recommended that the SN75C1154 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

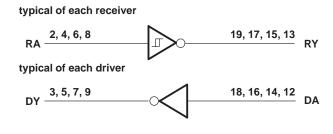
The SN75C1154 is characterized for operation from 0°C to 70°C.

## logic symbol†



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

## logic diagram (positive logic)

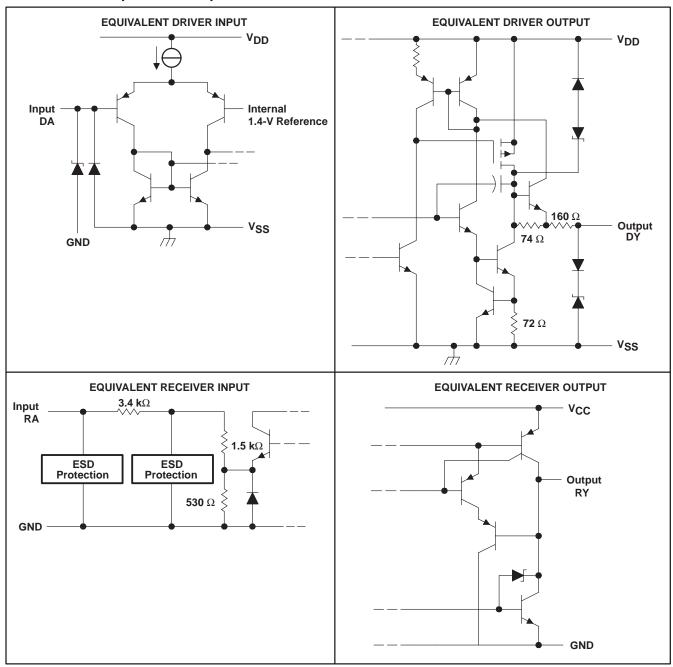




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### schematics of inputs and outputs



Resistor values shown are nominal.



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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V <sub>DD</sub> (see Note 1)	15 V
Supply voltage, V <sub>SS</sub>	
Supply voltage, V <sub>CC</sub>	7 V
Input voltage range, V <sub>I</sub> : Driver	$V_{SS}$ to $V_{DD}$
Receiver	30 V to 30 V
Output voltage range, Vo: Driver	$\dots (V_{SS} - 6 \text{ V}) \text{ to } (V_{DD} + 6 \text{ V})$
Receiver	$-0.3 \text{ V to } (V_{CC} + 0.3 \text{ V})$
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub> : SN75C1154	0°C to 70°C
Storage temperature range, T <sub>stq</sub>	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to the network GND terminal.

### **DISSIPATION RATING TABLE**

PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING		
DW	1125 mW	9.0 mW/°C	720 mW		
N	1150 mW	9.2 mW/°C	736 mW		

### recommended operating conditions

		MIN	NOM	MAX	UNIT	
Supply voltage, V <sub>DD</sub>		4.5	12	15	15 V	
Supply voltage, VSS		-4.5	-12	-15	V	
Supply voltage, V <sub>CC</sub>		4.5	5	6	V	
Input voltage, V <sub>I</sub>	Driver	V <sub>SS</sub> +2		$V_{DD}$	V	
	Receiver			±25		
High-level input voltage, VIH	Driver	2			V	
Low-level input voltage, V <sub>IL</sub>	Driver			0.8	V	
High-level output current, IOH	Receiver			-1	mA	
High-level output current, IOL	Neceivei			3.2	mA	
Operating free-air temperature, TA		0		70	°C	

### **DRIVER SECTION**

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V2	High lovel output voltage	V <sub>IL</sub> = 0.8 V,	$R_L = 3 k\Omega$ ,	$V_{DD} = 5 V$ ,	V <sub>SS</sub> = -5 V	4	4.5		V
VOH	High-level output voltage	See Figure 1		$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$	10	10.8		V
VOL	Low-level output voltage	V <sub>IH</sub> = 2 V,	$R_L = 3 k\Omega$ ,	$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 2)	See Figure 1		$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		-10.7	-10	v
lн	High-level input current	V <sub>I</sub> = 5 V,	See Figure 2					1	μΑ
IլL	Low-level input current	V <sub>I</sub> = 0,	See Figure 2					-1	μΑ
IOS(H)	High-level short circuit output current‡	V <sub>I</sub> = 0.8 V,	$V_O = 0$ or $V_{SS}$ ,	See Figure 1		-7.5	-12	-19.5	mA
IOS(L)	Low-level short circuit output current‡	V <sub>I</sub> = 2 V,	$V_O = 0$ or $V_{DD}$ ,	See Figure 1		7.5	12	19.5	mA
Inn	Supply current from VDD	No load All inn	ute at 2 \/ or 0 9 \/	$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		115	250	
IDD	Зарріў сапені поні УДД	No load, All inputs at 2 V or 0.8 V		V <sub>DD</sub> = 12 V	$V_{SS} = -12 \text{ V}$		115	250	μΑ
loo	Supply current from VSS	No load All inn	ute at 2 \/ or 0 9 \/	$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		-115	-250	
Iss	Supply current from VSS	No load, All inputs at 2 V or 0.8 V		V <sub>DD</sub> = 12 V	$V_{SS} = -12 \text{ V}$		-115	-250	μΑ
r <sub>O</sub>	Output resistance	$V_{DD} = V_{SS} = V_{DD}$	$V_{CC} = 0,  V_{O} = -1$	2 V to 2 V,	See Note 3	300	400		Ω

 $<sup>\</sup>frac{1}{1}$  All typical values are at  $T_A = 25$ °C.

NOTES: 2. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

3. Test conditions are those specified by EIA/TIA-232-E.

## switching characteristics, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm 10\%$ , $T_A$ = 25°C

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
<sup>t</sup> PLH	Propagation delay time, low- to high-level output§					1.2	3	μs
tPHL	Propagation delay time, high- to low-level output§	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	CL = 15 pF,	See Figure 3		2.5	3.5	μs
tTLH	Transition time, low- to high-level output¶				0.53	2	3.2	μs
tTHL	Transition time, high- to low-level output¶				0.53	2	3.2	μs
tTLH	Transition time, low- to high-level output#	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	$C_L = 2500 \text{ pF},$	See Figure 3		1	2	μs
tTHL	Transition time, high- to low-level output#	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	C <sub>L</sub> = 2500 pF,	See Figure 3		1	2	μs
SR	Output slew rate	$R_L = 3 \text{ to } 7 \text{ k}\Omega$ ,	CL = 15 pF,	See Figure 3	4	10	30	V/μs

<sup>§</sup> tpHL and tpLH include the additional time due to on-chip slew rate control and are measured at the 50% points.



<sup>‡</sup> Not more than one output should be shorted at one time.

Measured between 10% and 90% points of output waveform.

<sup>#</sup> Measured between 3 V and -3 V points of output waveform (EIA/TIA-232-E conditions) with all unused inputs tied either high or low.

### RECEIVER SECTION

## electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

	PARAMETER		TEST CON	NDITIONS		MIN	TYP†	MAX	UNIT
V <sub>IT+</sub>	Positive-going input threshold voltage	See Figure 5				1.7	2.1	2.55	٧
VIT-	Negative-going input threshold voltage	See Figure 5	See Figure 5			0.65	1	1.25	٧
V <sub>hys</sub>	Input hysteresis voltage (V <sub>IT+</sub> - V <sub>IT-</sub> )					600	1000		mV
		V <sub>I</sub> = 0.75 V,	$I_{OH} = -20  \mu A$	See Figure 5	and Note 4	3.5			
	High-level output voltage			V <sub>CC</sub> = 4.5 V		2.8	4.4		V
VOH		$V_I = 0.75 \text{ V},  I_{OH} = -1 \text{ m/s}$ See Figure 5	$I_{OH} = -1 \text{ mA},$	V <sub>CC</sub> = 5 V		3.8	4.9		V
		See Figure 5		V <sub>CC</sub> = 5.5 V		4.3	5.4		
VOL	Low-level output voltage	V <sub>I</sub> = 3 V,	I <sub>OL</sub> = 3.2 mA,	See Figure 5			0.17	0.4	V
1.	I Pak Java Canada amand	V <sub>I</sub> = 25 V				3.6	4.6	8.3	
ľІН	High-level input current	V <sub>I</sub> = 3 V				0.43	0.55	1	4
	Law law library and a constant	V <sub>I</sub> = −25 V				-3.6	-5	-8.3	mA
¹IL	Low-level input current	V <sub>I</sub> = -3 V		-0.43	-0.55	-1			
IOS(H)	Short-circuit output at high level	V <sub>I</sub> = 0.75 V,	V <sub>O</sub> = 0,	See Figure 4			-8	-15	mA
IOS(L)	Short-circuit output at low level	VI = VCC,	VO = VCC	See Figure 4			13	25	mA
laa	Cupply ourrent from Voc	No load,		$V_{DD} = 5 V$ ,	$V_{SS} = -5 \text{ V}$		400	600	
Icc	Supply current from V <sub>CC</sub>	All inputs at 0	or 5 V	V <sub>DD</sub> = 12 V,	V <sub>SS</sub> = -12 V		400	600	μΑ

<sup>†</sup> All typical values are at  $T_A = 25$ °C.

NOTE 4: If the inputs are left unconnected, the receiver interprets this as an input low and the receiver outputs will remain in the high state.

## switching characteristics, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10%, $T_A$ = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output				3	4	μs
tPHL	Propagation delay time, high- to low-level output	$C_L = 50 \text{ pF},  R_L = 5 \text{ k}\Omega,$	s, See Figure 6		3	4	μs
<sup>t</sup> TLH	Transition time, low- to high-level output				300	450	ns
tTHL	Transition time, high- to low-level output				100	300	ns
t <sub>w(N)</sub>	Duration of longest pulse rejected as noise‡	$C_L = 50 \text{ pF},  R_L = 5 \text{ k}\Omega$		1		4	μs

 $<sup>\</sup>pm$  The receiver ignores any positive- or negative-going pulse that is less than the minimum value of  $t_{W(N)}$  and accepts any positive- or negative-going pulse greater than the maximum of  $t_{W(N)}$ .

### PARAMETER MEASUREMENT INFORMATION

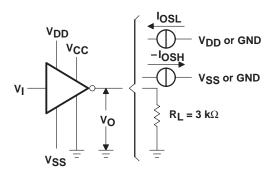


Figure 1. Driver Test Circuit  $V_{OH}$ ,  $V_{OL}$ ,  $I_{OSL}$ ,  $I_{OSH}$ 

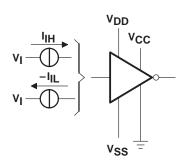
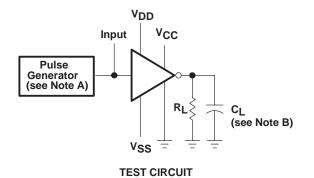
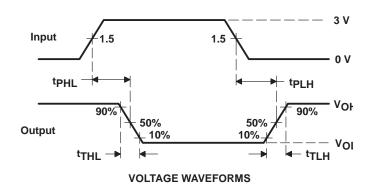


Figure 2. Driver Test Circuit, I<sub>IL</sub>, I<sub>IH</sub>

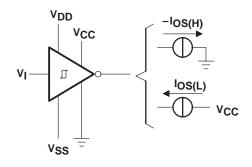




NOTES: A. The pulse generator has the following characteristics:  $t_W$  = 25  $\mu$ s, PRR = 20 kHz,  $Z_O$  = 50  $\Omega$ ,  $t_f$  =  $t_f$  < 50 ns.

B. C<sub>L</sub> includes probe and jig capacitance.

Figure 3. Driver Test Circuit and Voltage Waveforms





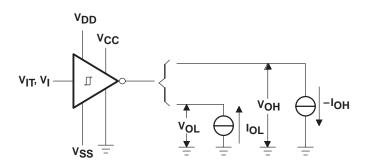
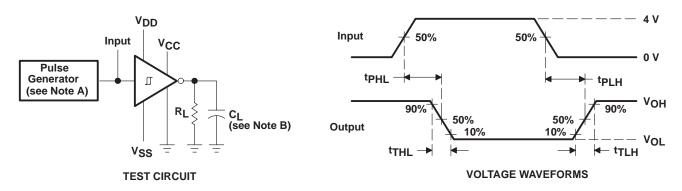


Figure 5. Receiver Test Circuit, VIT, VOL, VOH

### PARAMETER MEASUREMENT INFORMATION



NOTES: A. The pulse generator has the following characteristics:  $t_W$  = 25  $\mu$ s, PRR = 20 kHz,  $Z_O$  = 50  $\Omega$ ,  $t_\Gamma$  =  $t_f$  < 50 ns.

B. C<sub>L</sub> includes probe and jig capacitance.

Figure 6. Receiver Test Circuit and Voltage Waveforms

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